

FORM PTO-1449				Atty. Docket No. XA-9801A XA-9801B		Appl. No. 10/673,217	
LIST OF DOCUMENTS CITED BY APPLICANT				Applicant Atsushi KUROKAWA et al.			
				Filing Date HEREWITH 9-30-03		Group 2829	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
CC	AA	5,077,231	12/31/91	Plumton et al.	438	170	
CC	AB	5,166,083	11/24/92	Bayraktaroglu	438	170	
CC	AC	5,268,315	12/07/93	Prasad et al.	438	314	
CC	AD	5,324,671	06/28/94	Bayraktaroglu	438	317	
CC	AE	5,672,522	09/30/97	Streit et al.	438	312	
	AF						
	AG						
	AH						
	AI						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
CC	AJ	2001-210723	08/03/01	Japan			Abstract
	AK						
	AL						
	AM						
	AN						
	AO						
OTHER (including author, title, date, pertinent pages, etc.)							
CC	AP	Chen et al., "High-Speed InGaP/GaAs HBT's Using a Simple Collector Undercut Technique to Reduce Base-Collector Capacitance," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 7, July 1997, pp. 355-357.					
CC	AQ	Ahmari et al., "InGaP/CaAs Heterojunction Bipolar Transistor Grown on a Semi-Insulating InGaP Buffer Layer," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 11, November 1997, pp. 559-561.					
	AR						
Examiner Chandra Chaudhari				Date Considered 2-05			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							